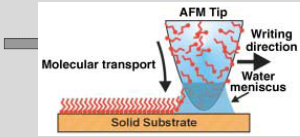
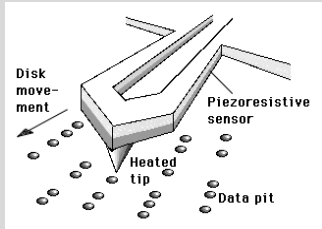
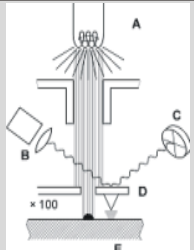
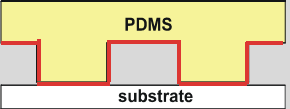
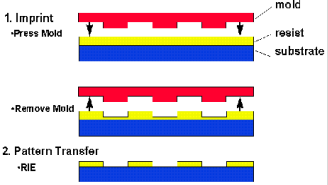
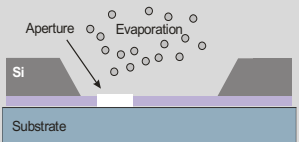
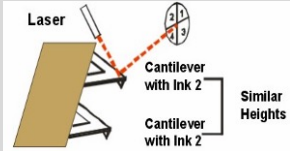
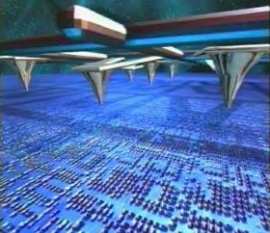
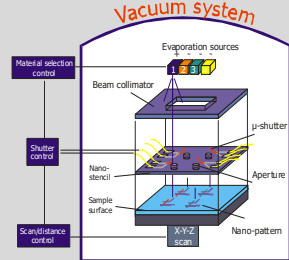
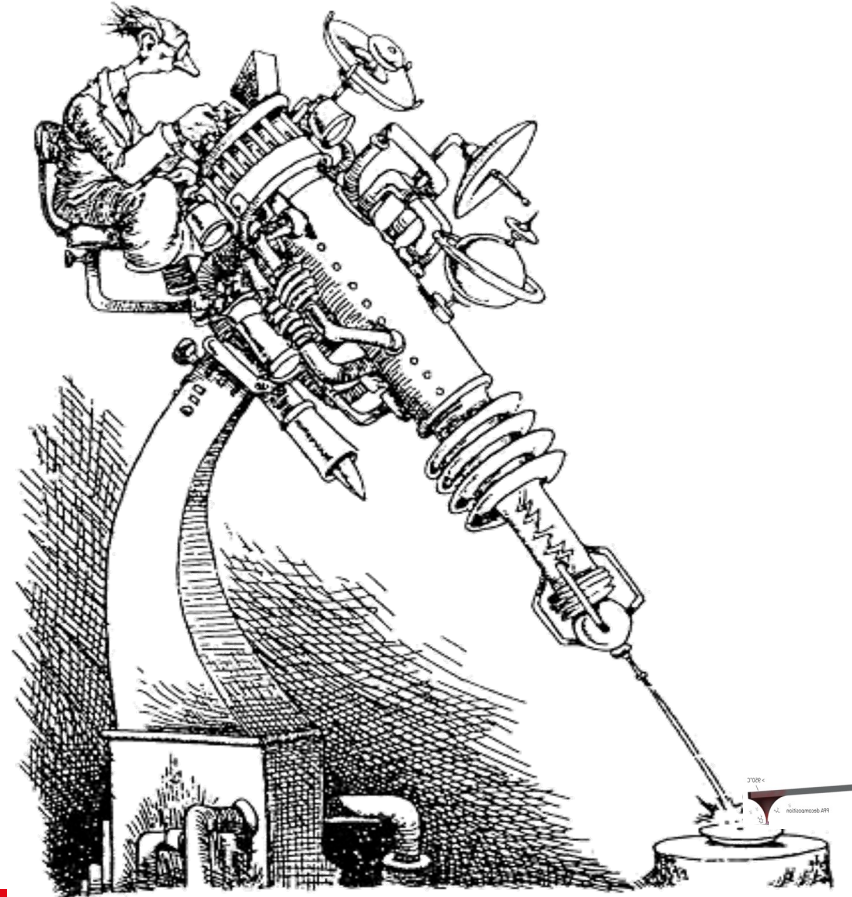


	Molecule Delivery Wet, soft-contact, 100 nm scale	Thermo-mechanical Nano-imprint, embossing, hard contact, 10 nm scale	Local Deposition Stencil, vacuum, no contact 10-100 nm scale
Single & Scanning <i>de novo</i>	 DipPen NADIS 	 Heated AFM 	AFM Nanostencil 
Parallel & Static <i>Replication</i>	Soft-lithography 	NIL 	Membrane Nano-stencil 
Parallel & Scanning <i>Adaptive mass-production</i>	Parallel NADIS 	 Millipede 	Smart Stencil 



Thermal Scanning Probe Lithography

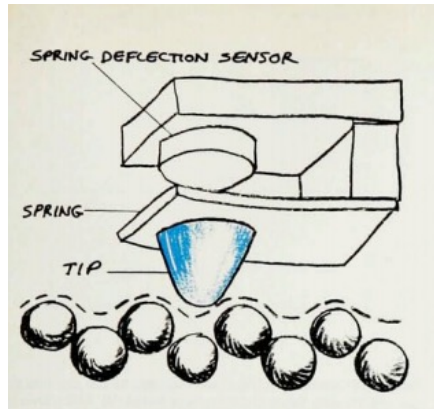
Patterning with heat only

ATOMIC FORCE MICROSCOPY

It is surprisingly easy to make a cantilever with a spring constant weaker than the equivalent spring between atoms, allowing a sharp tip to image both conducting and nonconducting samples at atomic resolution.

Daniel Rugar and Paul Hansma

1990 American Institute of Physics
PHYSICS TODAY OCTOBER 1990

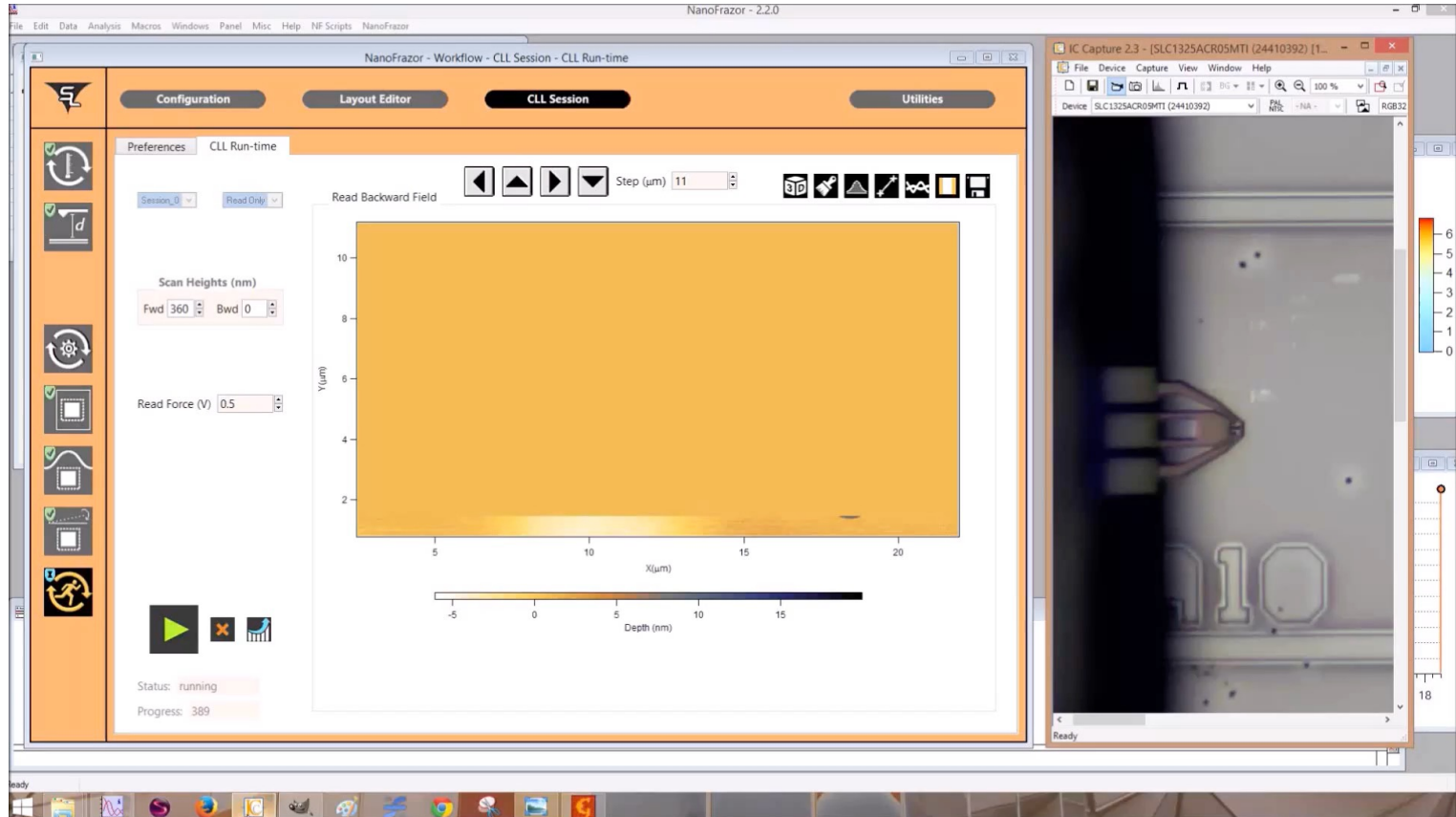




1000 deg C
10 nm
1 μ s

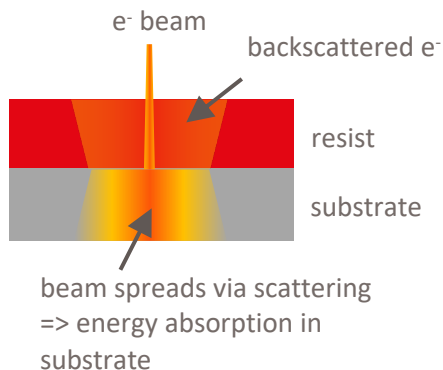
IBM, Swisslitho, Heidelberg

Modern t-SPL system (closed loop)



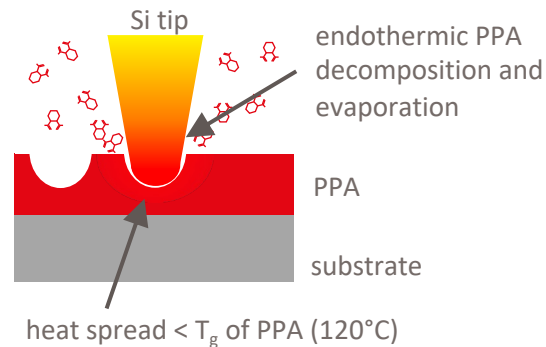
What makes t-SPL unique, specific w/r to EBL ?

Electron Beam Lithography



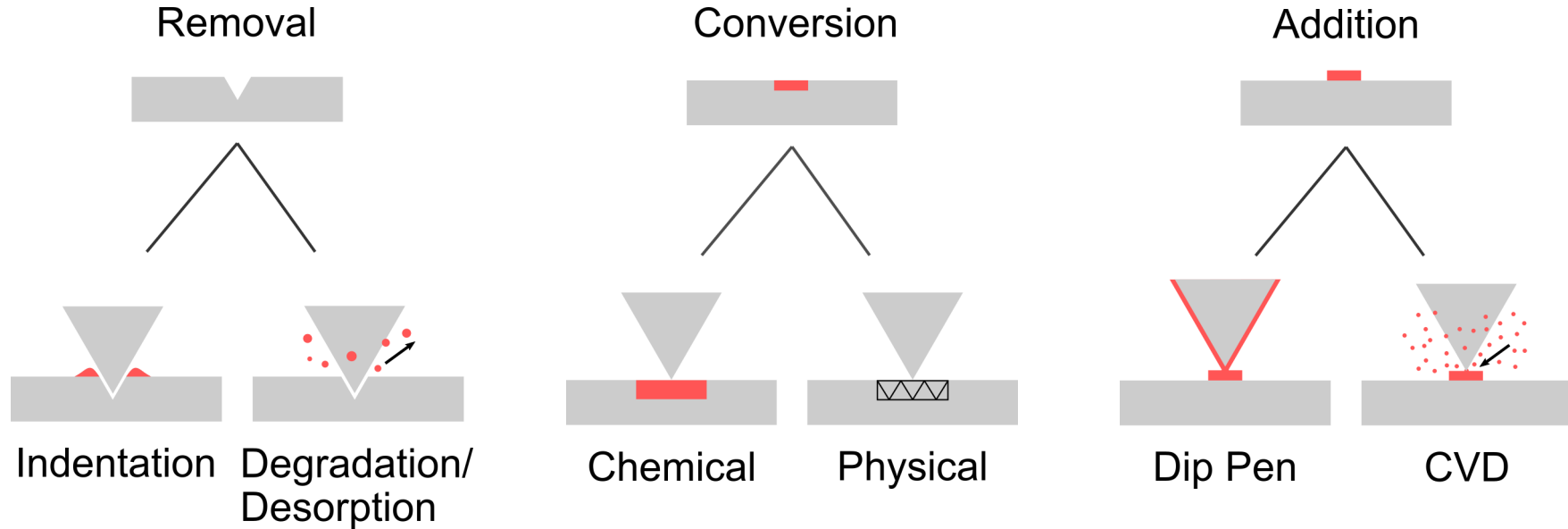
Possible damage of the substrate by lattice defects, vacancies or trapped charges
2D materials, organic molecules, dielectrics

T-SPL

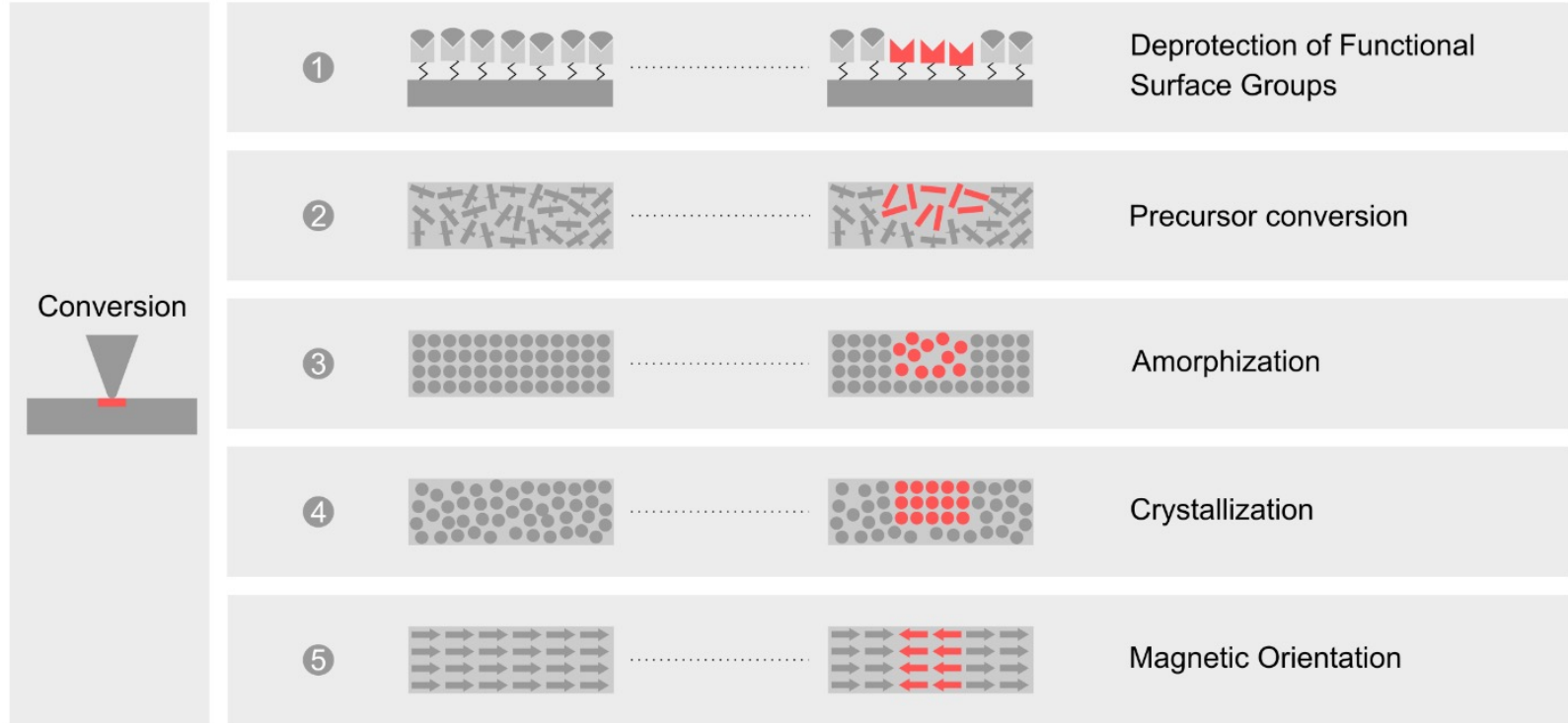


The substrate is hardly heated (in particular for substrates with a high heat conductivity or when a hard mask is applied under the PPA) and hence **not damaged**

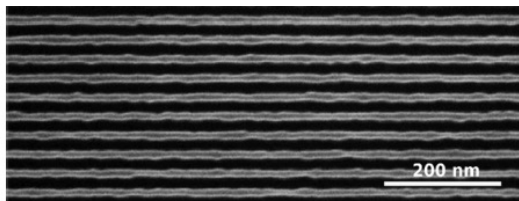
T-SPL surface patterning



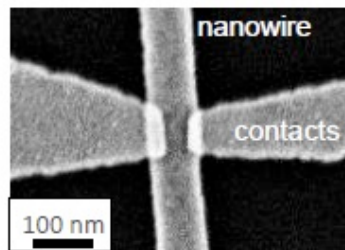
Conversion



Typical t-SPL device fabrication



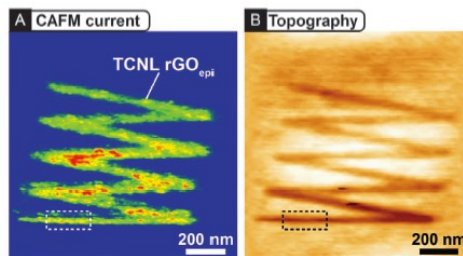
10-20 nm half-pitch into Si
Cho et al. ACS Nano 2017



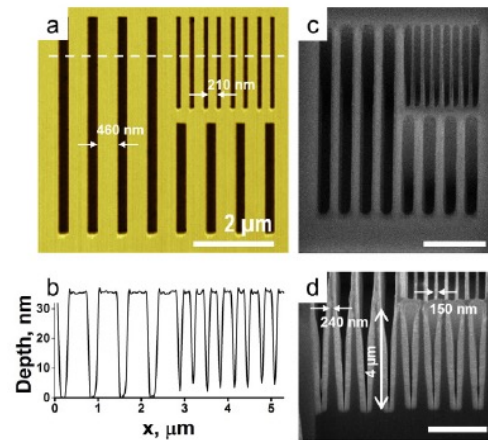
Side gates, contacts on nanowire

Lift-off

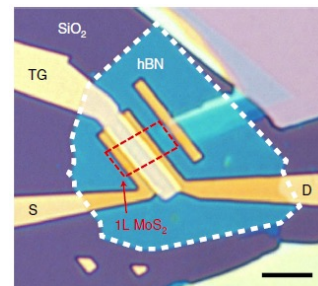
Wolf et al. J. Vac. Sci. Tech. B 2015,



Graphene, oxidation
Wei et al. Science 2010, 328, 1373



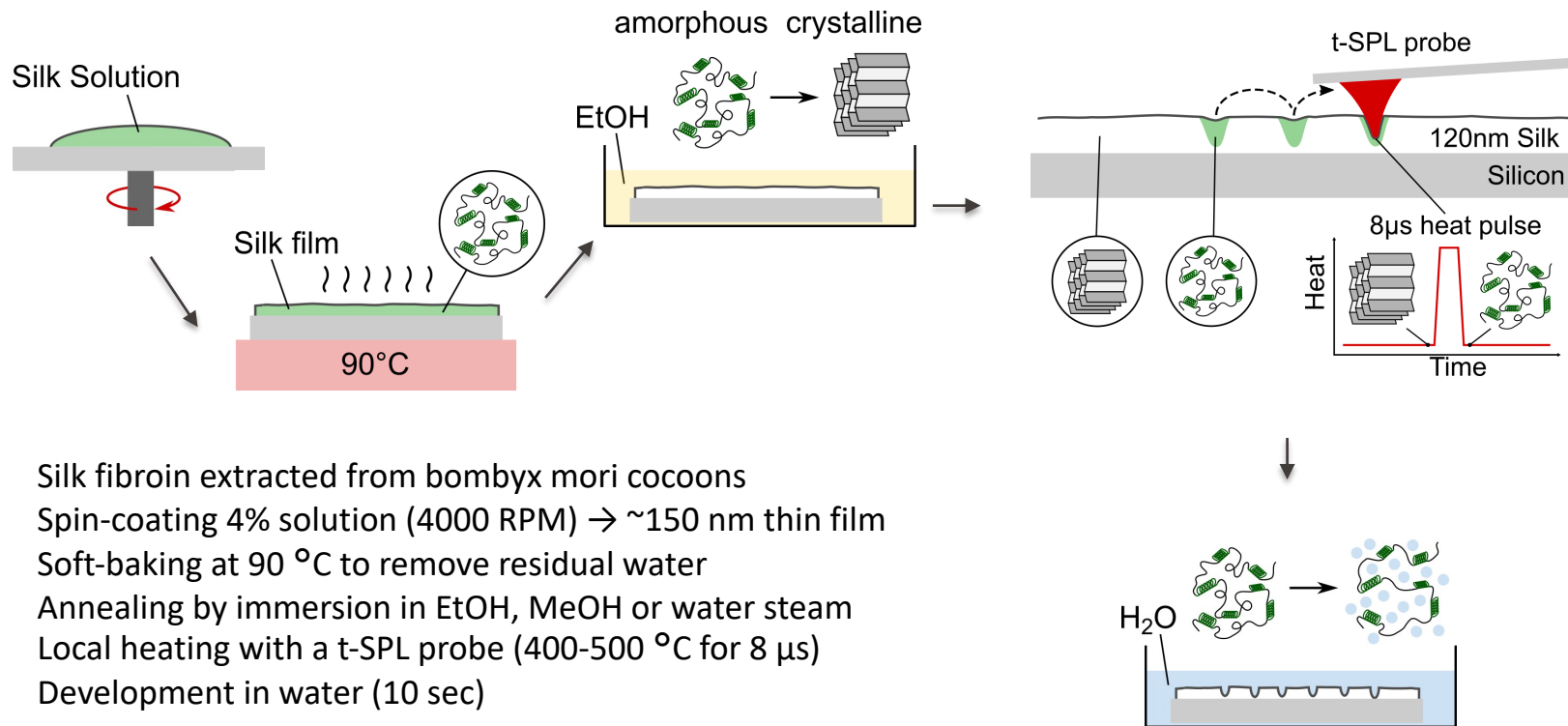
Dry Etching amplification, high aspect ratio
Lisunova et al. MEE 2017



2D material electronics
Zheng et al. Nature Electronics 2019

Nanopatterning in silk using T-SPL

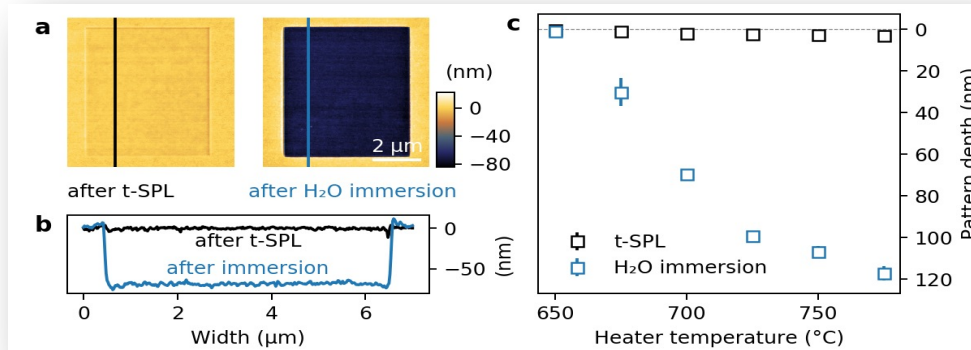
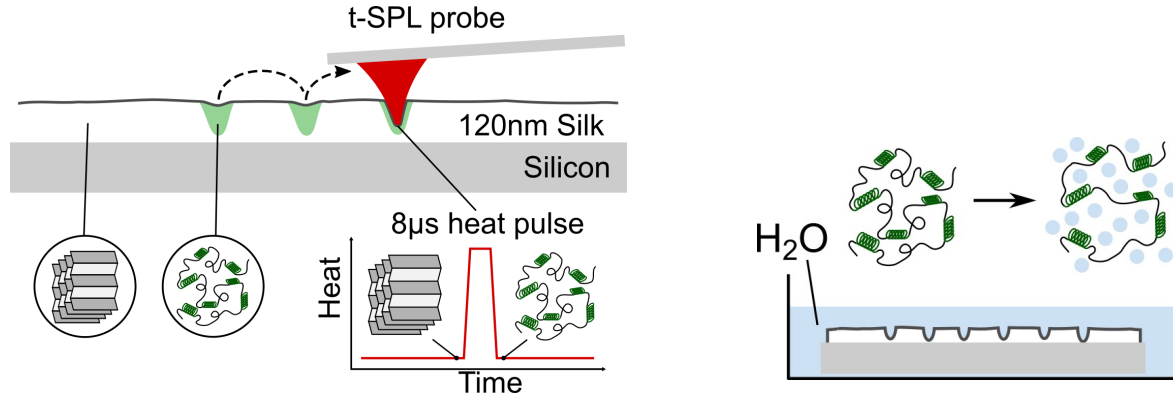
$E_{\text{silk}} = 1\text{-}8 \text{ GPa}$; 90% transparent



- Silk fibroin extracted from bombyx mori cocoons
- Spin-coating 4% solution (4000 RPM) → ~150 nm thin film
- Soft-baking at 90 °C to remove residual water
- Annealing by immersion in EtOH, MeOH or water steam
- Local heating with a t-SPL probe (400-500 °C for 8 μs)
- Development in water (10 sec)

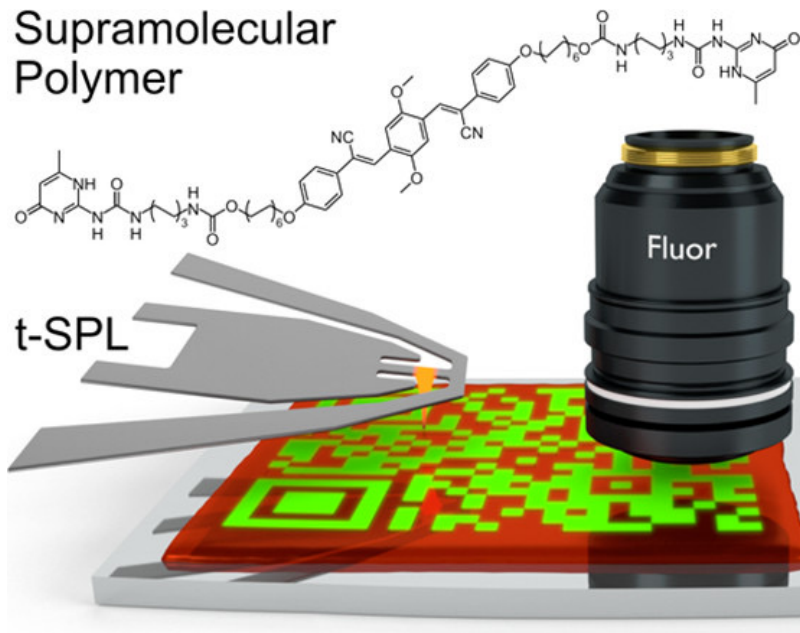
S. Howell et al., (in prep)

Nanopatterning in silk using T-SPL

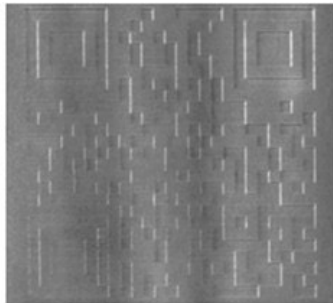


Silk as biomaterial has excellent properties for functional devices, sensors, actuators, medical implants.

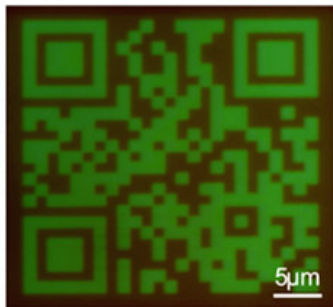
T-SPL on stimuli-responsive, thermochromic film



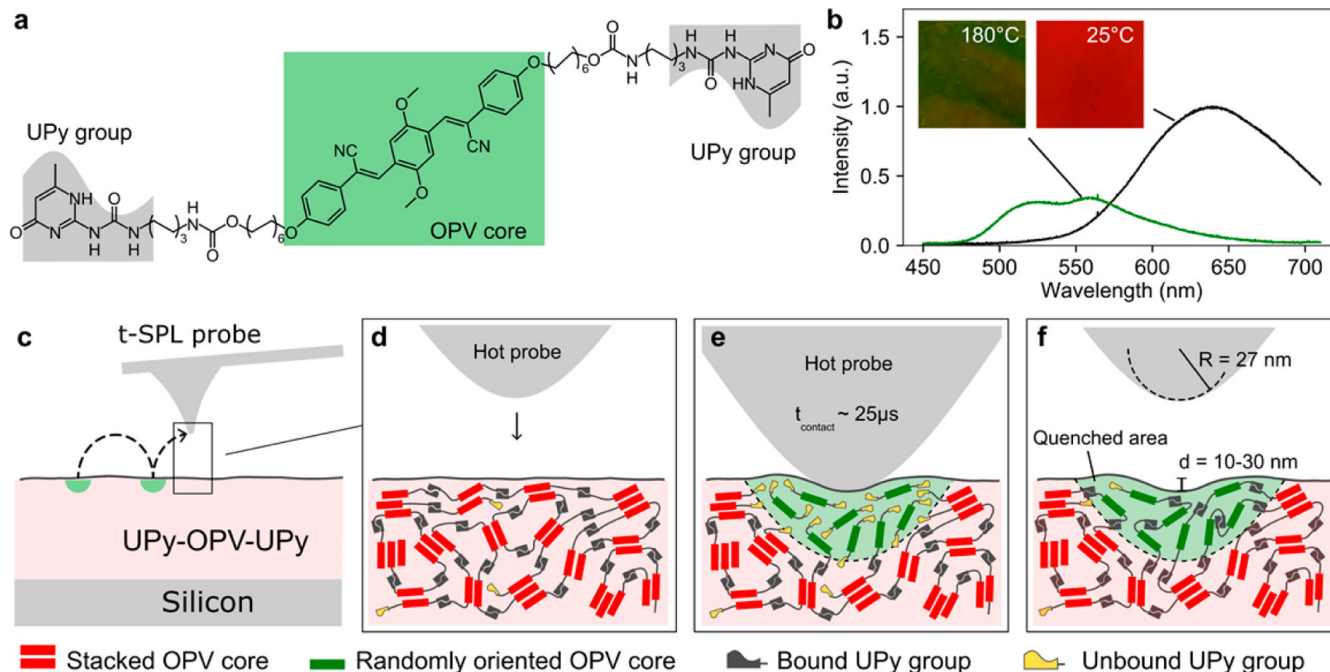
AFM



Fluorescence

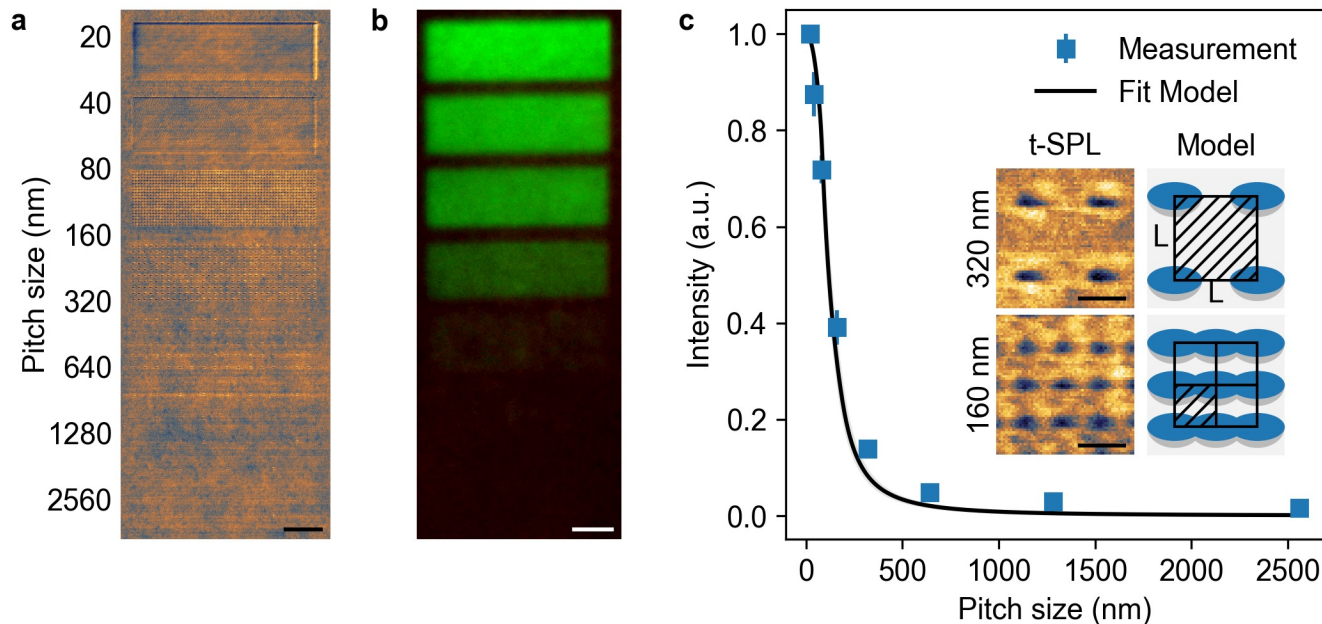


T-SPL on stimuli-responsive, thermochromic film



S. Zimmermann et al. ACS AMI (2017)

T-SPL on stimuli-responsive, thermochromic film

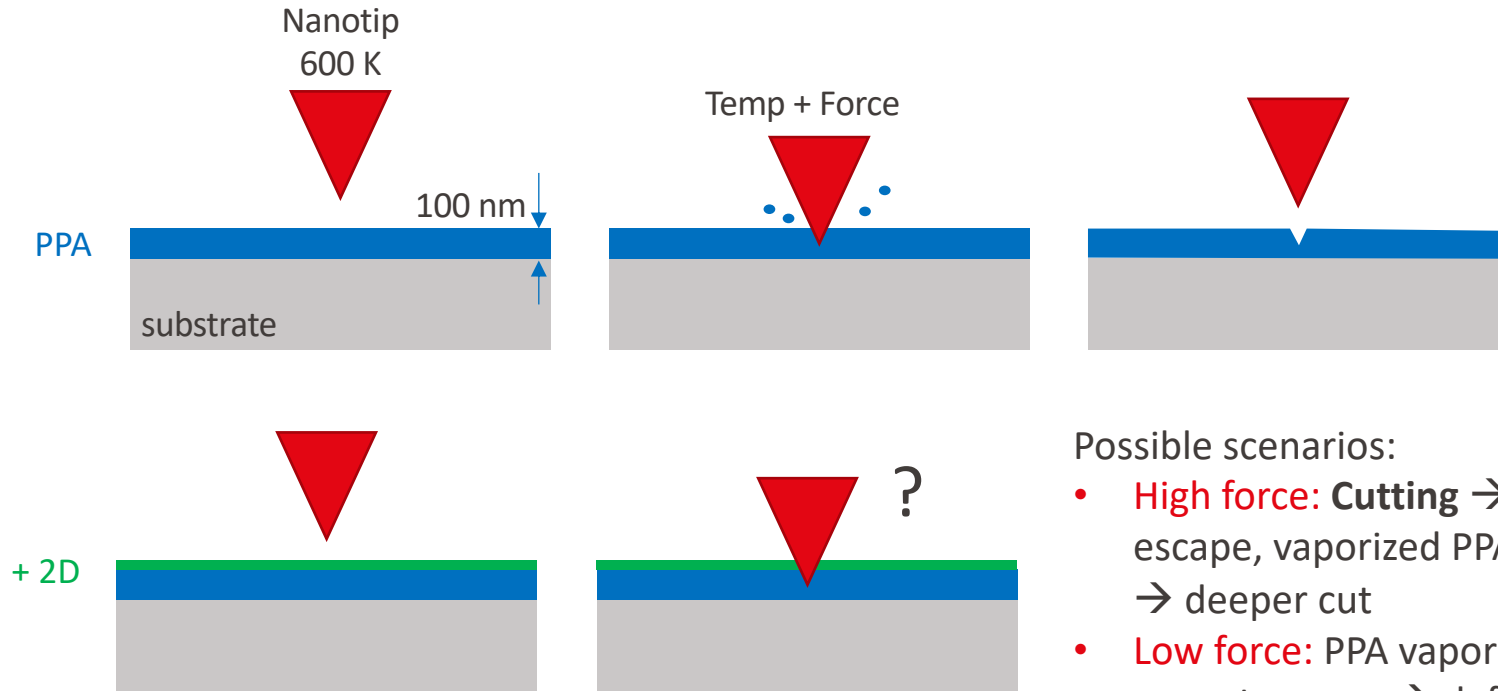


Shift from red to green fluorescence when heated

•
•
•
Kinetic trapping when cooled down fast (heater switched off)

With Adolphe Merkle Institute, Fribourg, Switzerland

Gedankenexperiment



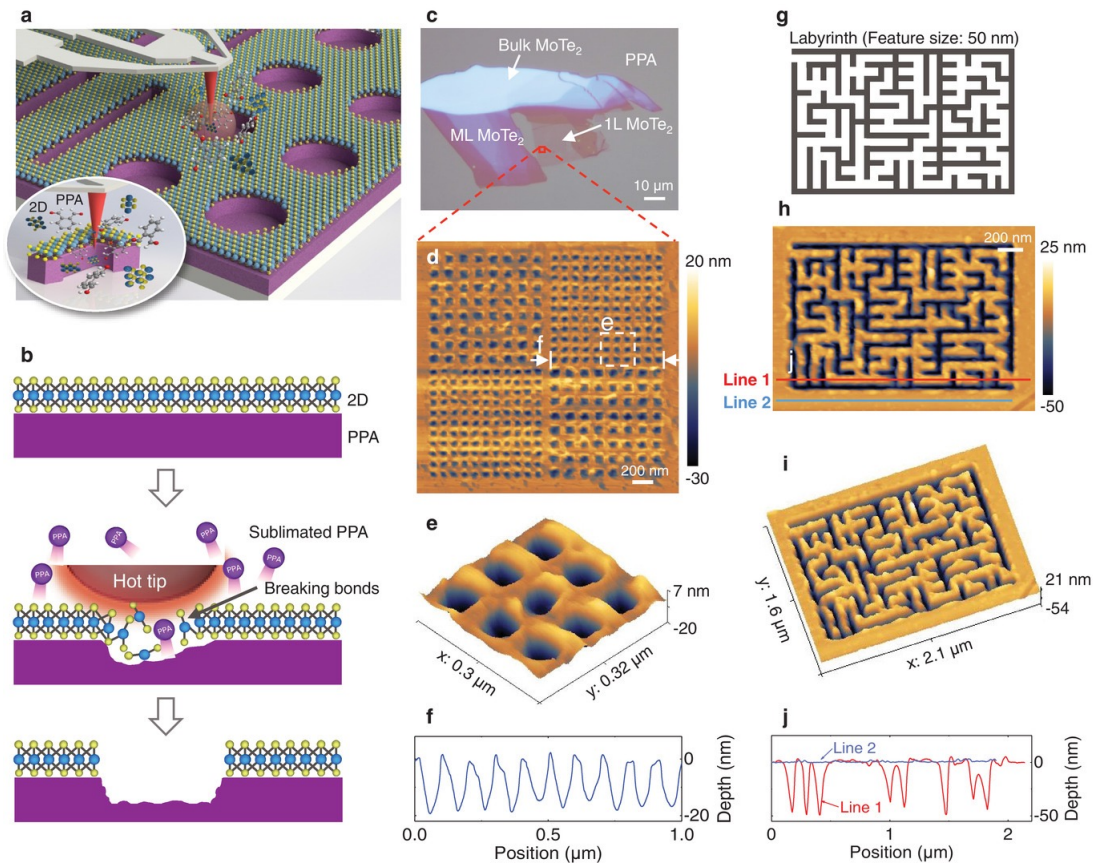
Possible scenarios:

- **High force: Cutting** → PPA can escape, vaporized PPA can escape → deeper cut
- **Low force:** PPA vaporizes but cannot escape → deformation → fast cooling → **Permanent Indentation**

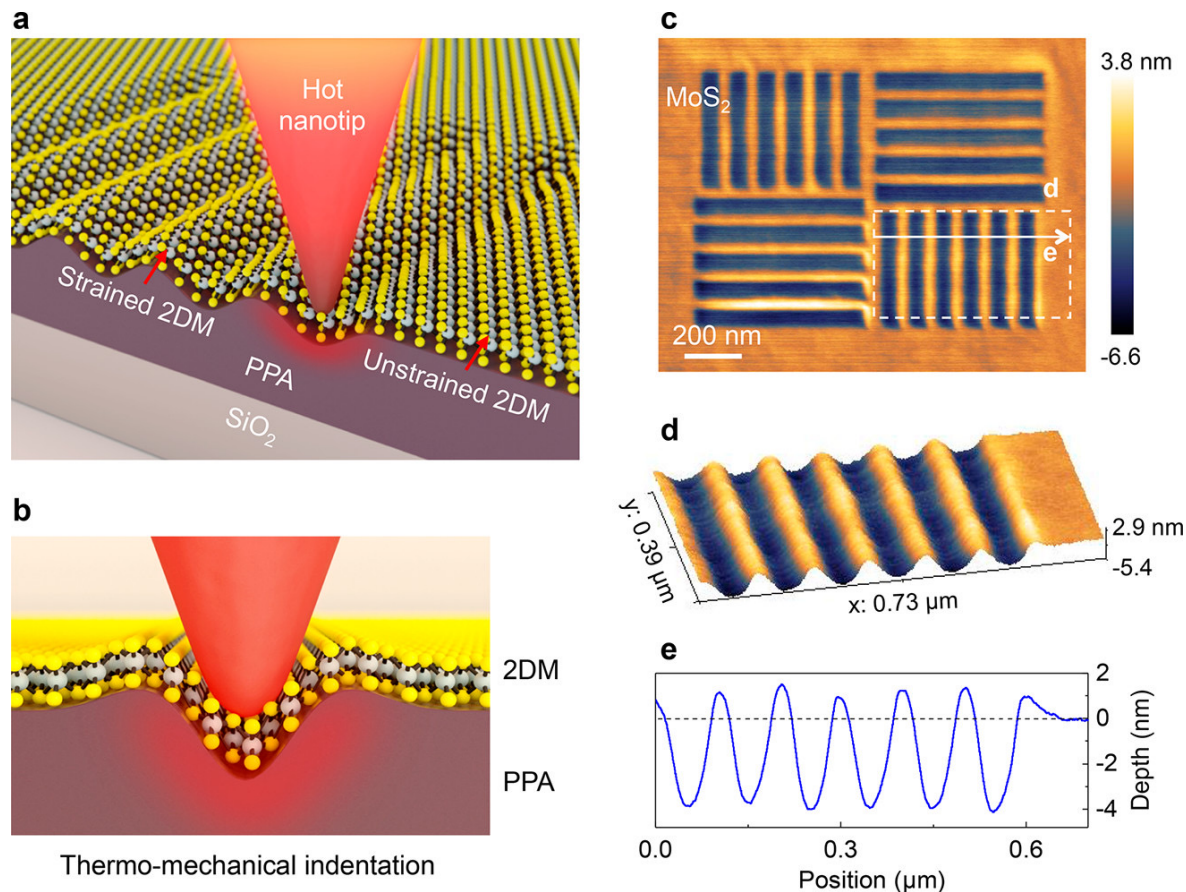
PPA: Polyphthalamide (thermal resist)

2D: ML of Graphene, MoS₂

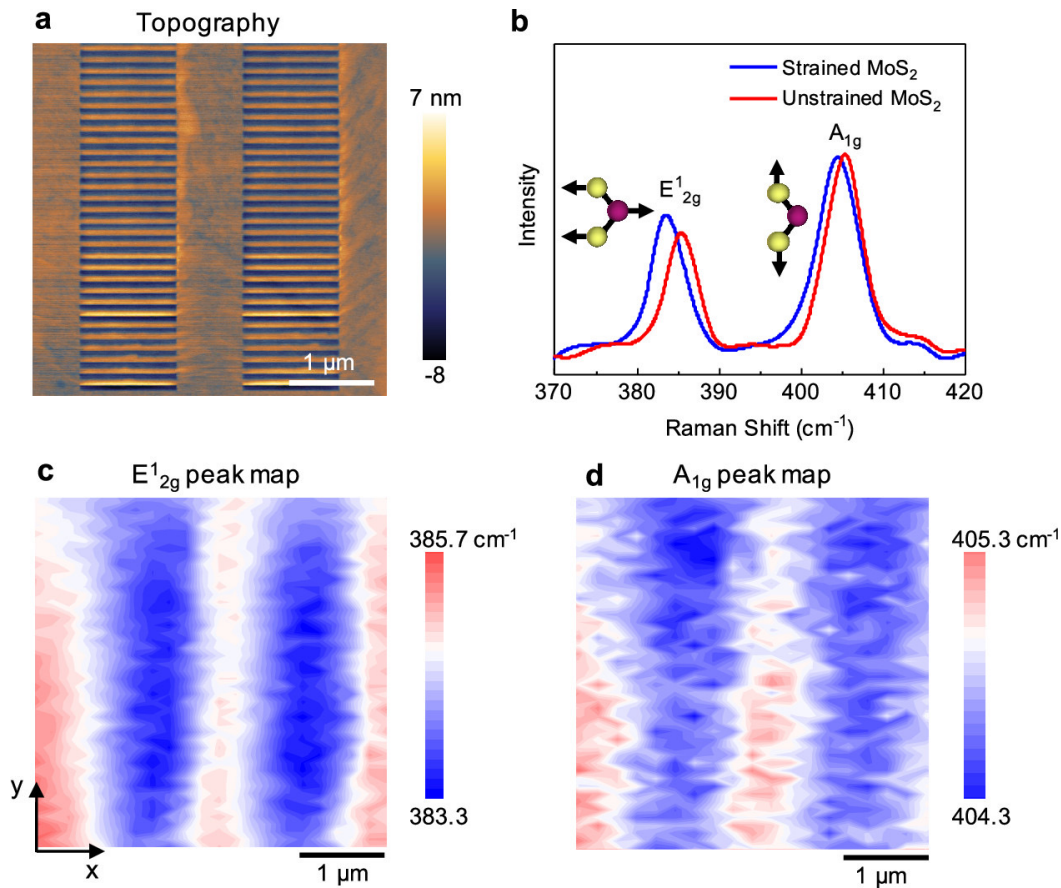
Direct nanocutting of 2D materials



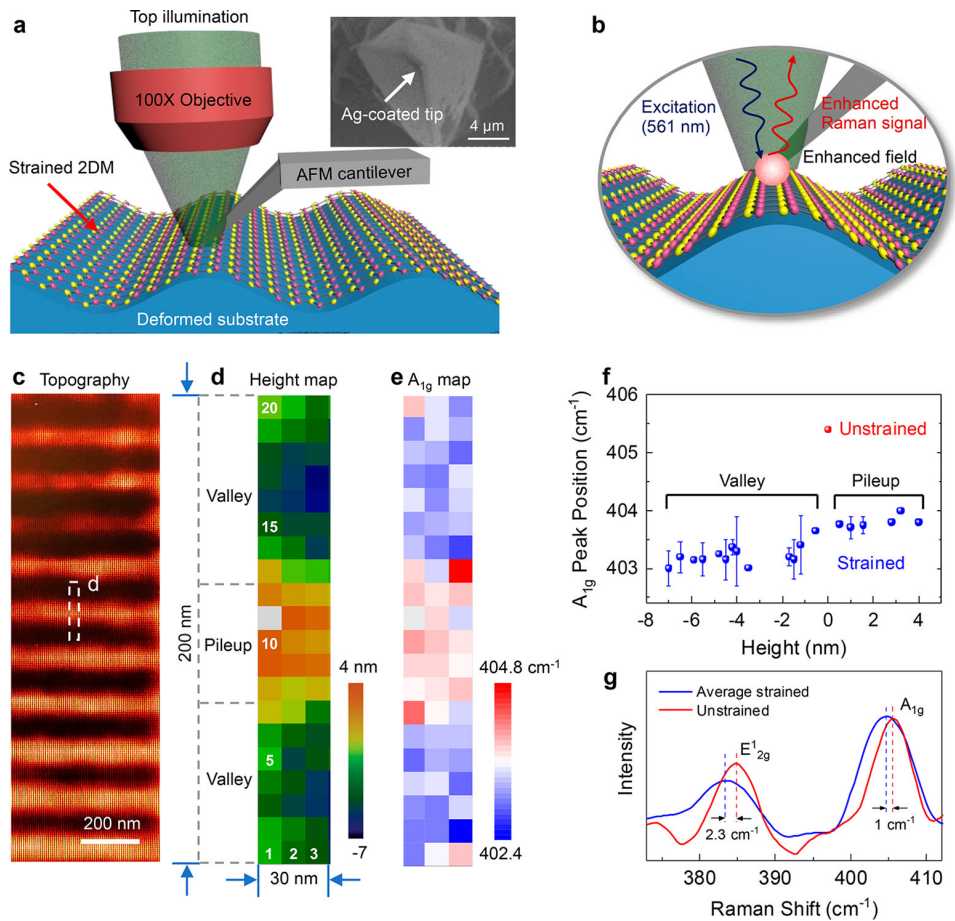
Straining of 2D materials at nanoscale



Straining of 2D materials at nanoscale



Straining of 2D materials at nanoscale



30 years of t-SPL .. and counting

